



ACGI053059-P41-1

C-band matched GaAs Device

Features:

Frequency: 5.3~5.9GHz

1dB Output Power : $P_{1dB}=41dBm$ (type)

PowerGain: Gain=9dB(type)

Add-Efficiency: PAE=35%(type)

Port matching: $Z_{in}/Z_{out}=50\Omega$

Description:

ACGI053059-P41-1 is an internal matching GaAs device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 5.3~5.9GHz. This device can be used in different RF/Microwave system and subsystem. The high output power level, high efficiency and wide operating temperature range can make application very flexible.

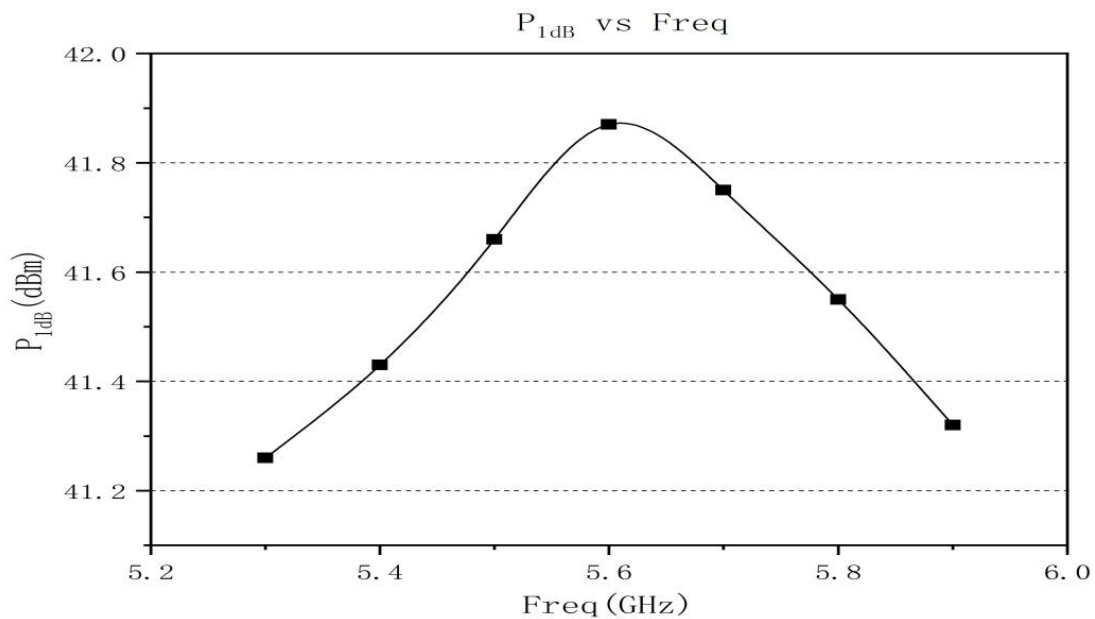
Maximun Ratings (TC=25°C, Not recommended working under this condition):

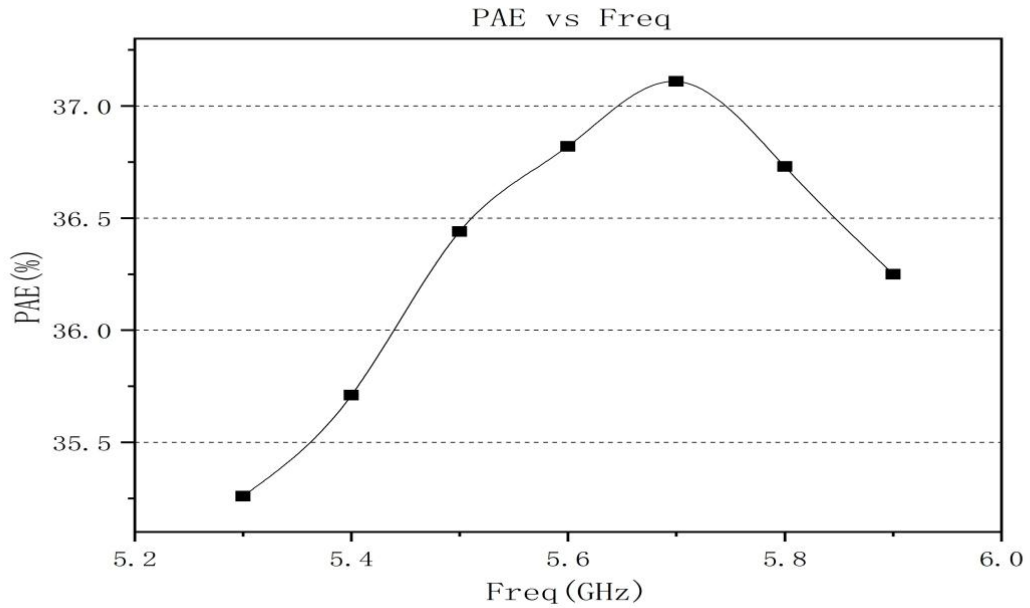
	Symbol	Value	Unit
Voltage between source and drain	V_{ds}	11	V
Voltage between gate and source	V_{gs}	-3	V
Storage Temperature Range	T_{stg}	-65 to +150	°C
Drain and Source Channel Temperature	T_{ch}	150	°C

Electrical Characteristics:

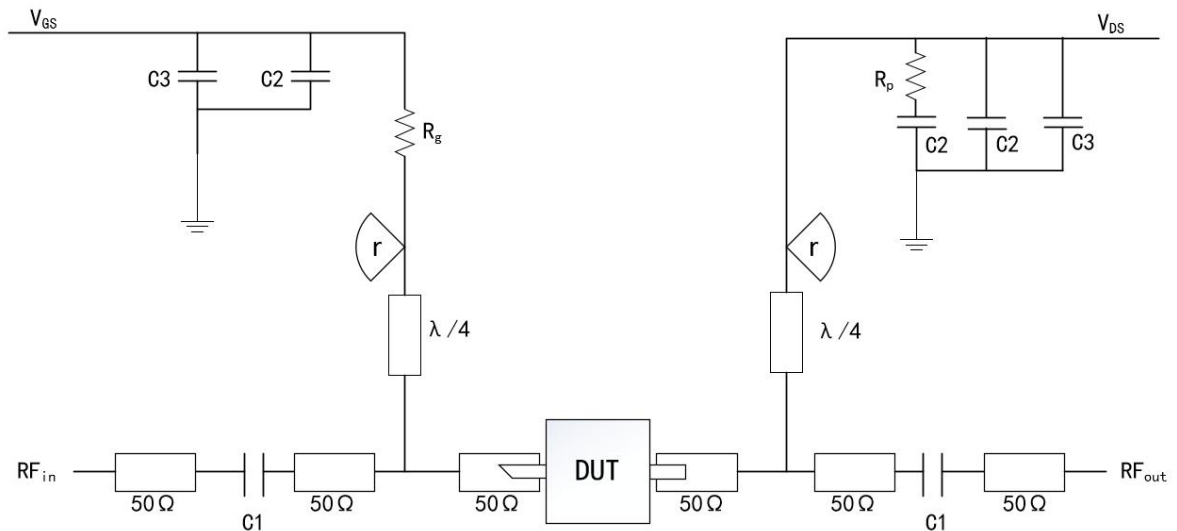
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I _{dsr}	V _{ds} =10V CW. P _{in} : 32dBm Freq: 5.3~5.9GHz	-	3.5	-	A
1dB output power	P _{1dB}		-	41	-	dBm
Gain	G _p		-	9	-	dB
Add-Efficiency	PAE		-	35	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





Application Circuit:



DUT: Device to be tested

C1:4.7pF

C2:1000pF

C3:100uF

Rp:51Ω

Rg:15Ω

r(radius)≈5.8mm(Rogers5880, 20mil)

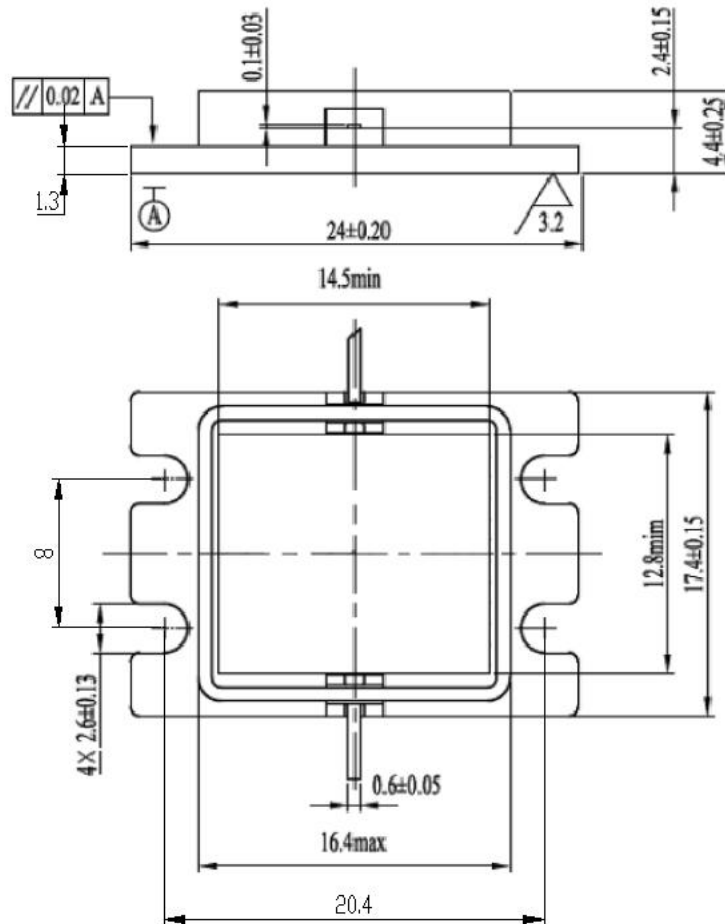
If you need more detailed product information, please contact our marketing personnel or designers.

Contact: Peter.Zhang Email: peter.zhang@anserrf.com

ESD Level:

ESD	Class III	2000V
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Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.